

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization  
International Bureau



(43) International Publication Date  
29 September 2005 (29.09.2005)

PCT

(10) International Publication Number  
**WO 2005/091391 A1**

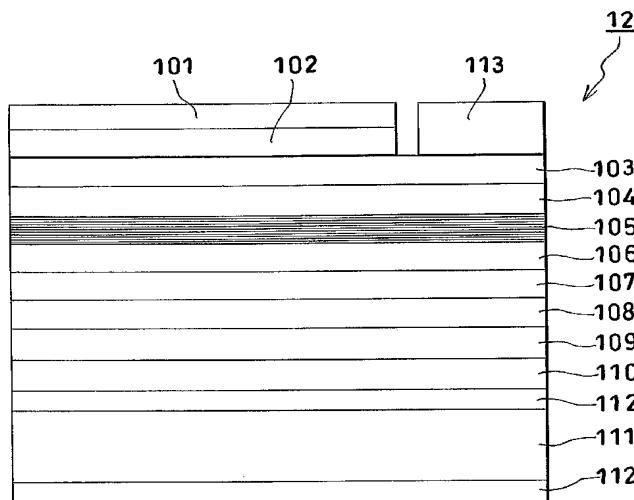
- (51) International Patent Classification<sup>7</sup>: **H01L 33/00**
- (21) International Application Number: PCT/JP2005/005448
- (22) International Filing Date: 17 March 2005 (17.03.2005)
- (25) Filing Language: English
- (26) Publication Language: English
- (30) Priority Data:  
2004-078819 18 March 2004 (18.03.2004) JP  
60/557063 29 March 2004 (29.03.2004) US
- (71) Applicant (for all designated States except US): **SHOWA DENKO K.K.** [JP/JP]; 13-9, Shiba Daimon 1-chome, Minato-ku, Tokyo 105-8518 (JP).
- (72) Inventors; and
- (75) Inventors/Applicants (for US only): **KUSUNOKI, Katsuki** [JP/JP]; c/o Showa Denko HD K.K., 5-1, Yawata Kaigan dori, Ichihara-Shi, Chiba 290-0067 (JP). **MITANI, Kazuhiro** [JP/JP]; c/o Showa Denko HD K.K., 5-1, Yawata Kaigan dori, Ichihara-Shi, Chiba 290-0067 (JP). **UDAGAWA, Takashi** [JP/JP]; C/o Showa Denko K.K., 1505, Shimokagemori, Chichibu-shi, Saitama 369-1871 (JP).
- (74) Agents: **FUKUDA, Kenzo** et al.; Kashiwaya Bldg., 6-13, Nishishinbashi 1-chome, Minato-ku, Tokyo 105-0003 (JP).
- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: GROUP III NITRIDE SEMICONDUCTOR LIGHT-EMITTING DEVICE AND METHOD OF PRODUCING THE SAME



(57) Abstract: A Group III nitride semiconductor light-emitting device includes a stacked structure 11 formed on a crystal substrate (100) to be removed from it and including two Group III nitride semiconductor layers 104 and 106 having different electric conductive types and a light-emitting layer 105 which is stacked between the two Group III nitride semiconductor layers and which includes a Group III nitride semiconductor, and a plate body 111 made of material different from that of the crystal substrate and formed on a surface of an uppermost layer which is opposite from the crystal substrate that is removed from the stacked structure.

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